

ABSTRACT OF THE DISCLOSURE

The present invention relates to a method and an apparatus for depositing a metal layer on a semiconductor structure. A semiconductor structure comprising at least one recess and at least one elevation is provided. The semiconductor structure is electroplated for depositing a layer of metal and for filling at least one recess with metal. The semiconductor structure is electropolished for preferentially removing the metal from at least one elevation, and chemical mechanical polishing is performed to remove a surplus of the metal from at least one elevation and for planarizing a surface of the semiconductor structure. The present invention advantageously allows the reduction of the demands on the chemical mechanical polishing process.